



The attenuator is designed for RF power level adjustment. SYMAIR RF attenuators have compact dimensions, stable power handling and high reliability for long-term applications. The attenuator has low-PIM performance, which avoids system interference.

*\*XX refers to the optional attenuation values.*

## General Specifications

Product Type	Low PIM RF Attenuator
Frequency Band	694-2700 MHz
Power Handling	5 Watts
Passive Intermodulation (3rd)	≤-150dBc@2×33dBm
Connector Interface	4.3-10 male to 4.3-10 female

## Electrical Specifications

Frequency Band	694-2700 MHz						
Return Loss	≤-19.1 dB						
VSWR	≤1.25						
Attenuation	3 dB	5 dB	6 dB	10 dB	15 dB	20 dB	30 dB
Accuracy	±1.5 dB	±1.5 dB	±1.5 dB	±1.6 dB	±1.8 dB	±1.8 dB	±1.8 dB
Passive Intermodulation (3rd)	≤-150dBc@2×33dBm						
Power Handling	5 watts						
Impedance	50 ohms						

## Material Specifications

Cavity	Cavity Enclosure	Aluminum alloy
	Cavity Outer Surface Treatment	Conductive oxidation / Painting
Connector	Cavity Inner Surface Treatment	Cu3Ag1
	Inner Conductor	Aluminum alloy
	Inner Conductor Surface Treatment	Ag1
	Outer Conductor	Brass
	Outer Conductor Surface Treatment	Tri-metal CuSnZn3
	Inner Conductor	Brass
	Inner Conductor Surface Treatment	Ag1
	Insulator	PTFE/TPX
	Gasket	Silicon rubber

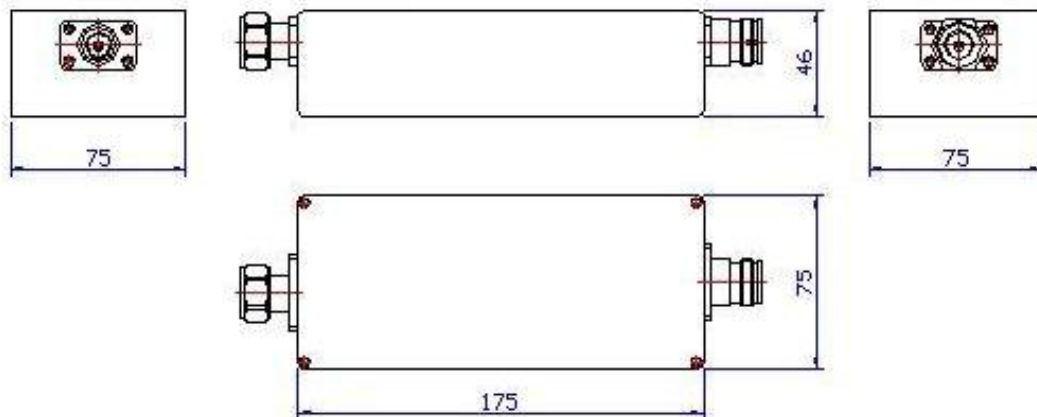
## Mechanical Specifications

Dimension	75×46×175 mm (Excluding connectors and brackets)
Weight	0.5 kg
Connectors Type	4.3-10 male to 4.3-10 female
Mounting	Plane
Packing	1pcs in box

## Environmental Specifications

Operating Temperature	-40 °C to +65 °C
Storage Temperature	-45 °C to +85 °C
Relative Humidity	5% - 95%
Application	Indoor

## Outline Drawing



## Regulatory Compliances

ISO 9001:2015	Compliant
ROHS	Compliant
China RoHS	Compliant
UK RoHS	Compliant
REACH	Compliant
EU/CE	Compliant

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